

DESCRIPTION

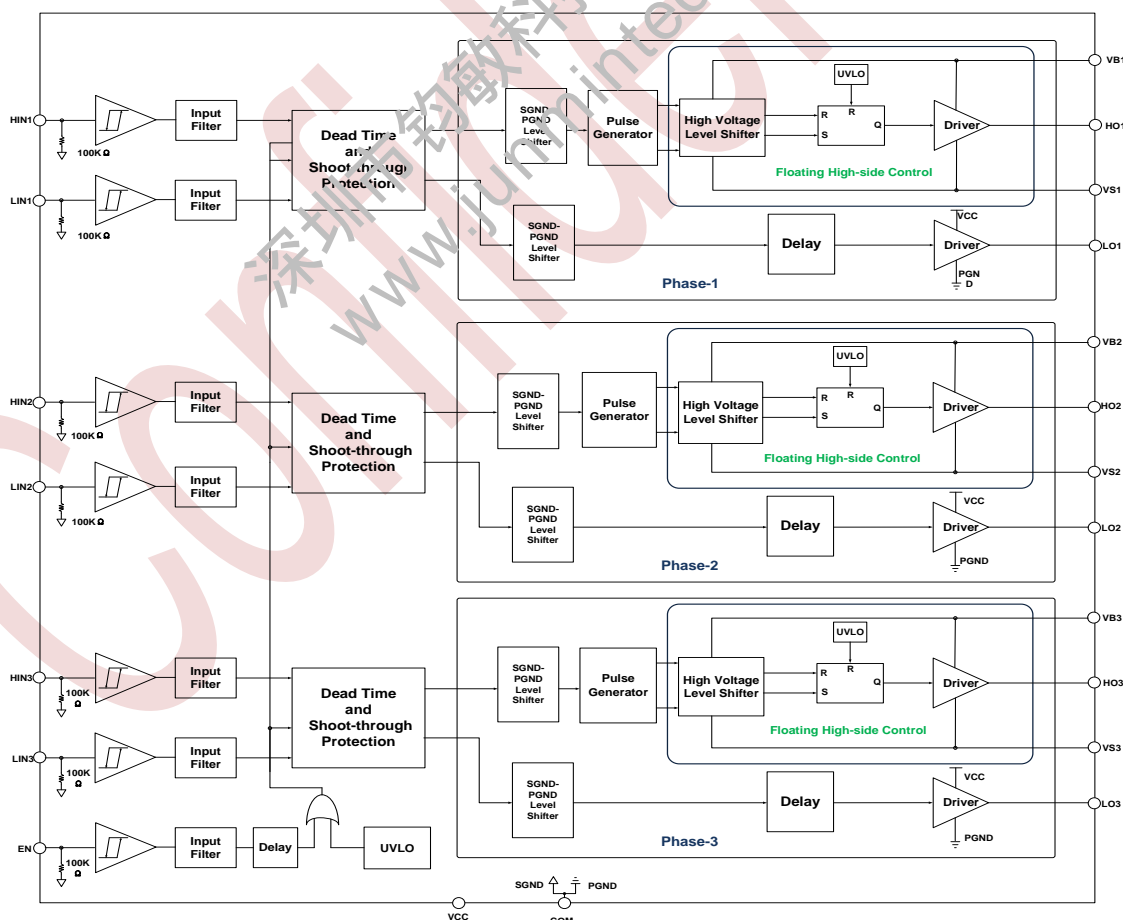
The PT5618 is a high speed power MOSFET and IGBT driver with three independent high and low side referenced output channels for 3-phase gate driver. Built-in dead time protection and Shoot-through protection that prevent half-bridge against damage.

The UVLO circuits prevent malfunction when VCC and VBS are lower than the specified threshold voltage. Novel high-voltage BCD process and common-mode noise canceling technique provide stable operation of high-side drivers under high-dv/dt noise circumstances and excellent negative transient voltage tolerance. PIN EN designed for standby mode can be used to enable chip into low quiescent current state and get long battery life time.

APPLICATIONS

- 3-phase Motor Driver for E-BIKE, electric power tool
- Mini/micro motor control powered by battery
- Home appliance fed by 110V-AC grid
- General purpose inverter

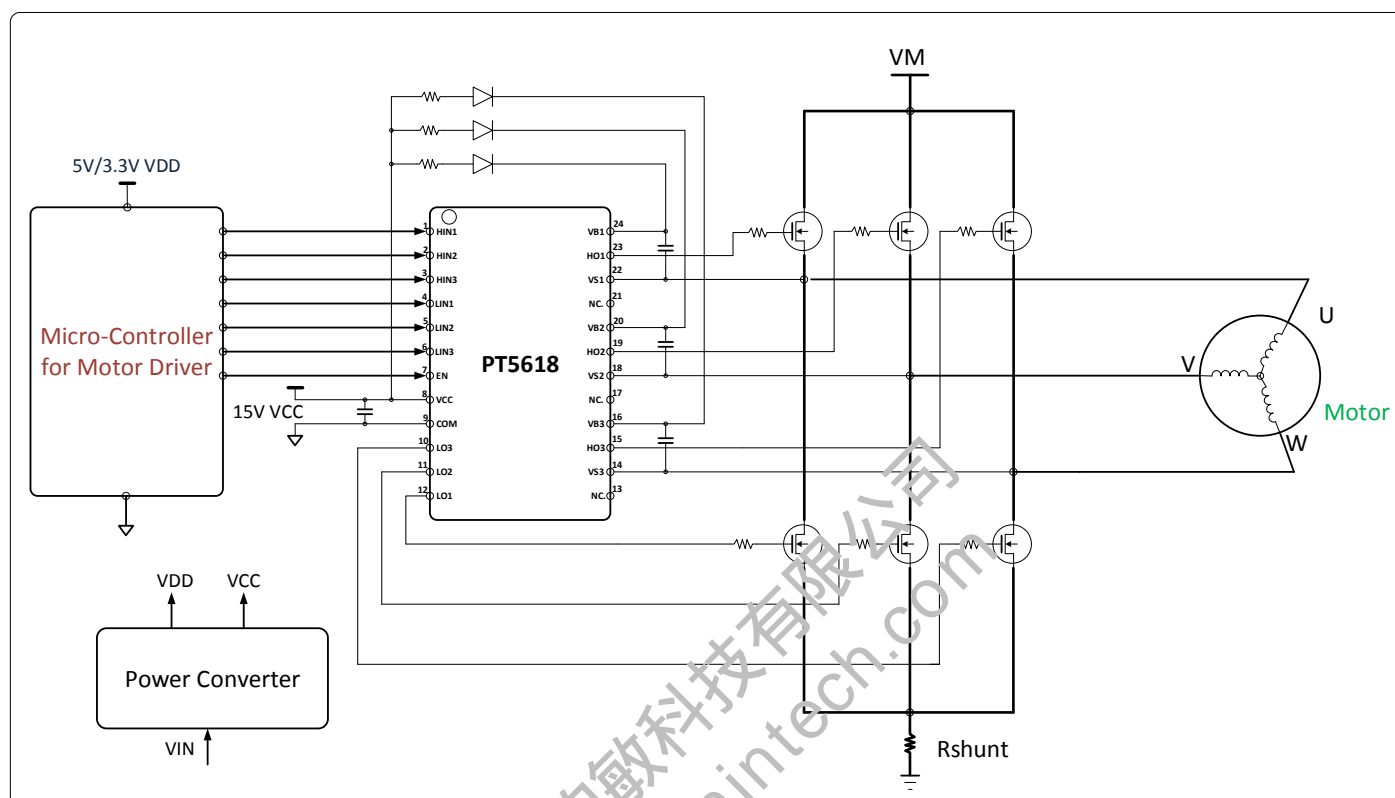
BLOCK DIAGRAM



FEATURES

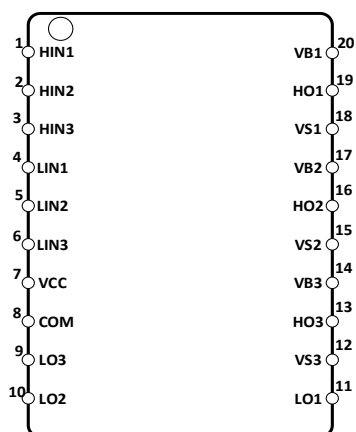
- Integrated 200V half-bridge high side driver
- Driver up to 3-phase half-bridge gates
- Built-in dead time control
- Shoot-through protection
- Under voltage lockout for VCC and VBS
- 3.3V, 5V, 15V input logic Compatible
- Built-in input filter
- Low standby current
- IO+/IO-: 320mA/620mA
- Built-in dead time: 0.55us(typ.)
- Common-Mode dv/dt Noise Canceling Circuit
- Tolerant to negative transient voltage
- Low di/dt gate drive for better noised immunity
- -40°C - 125°C operating range
- Small footprint package: TSSOP 20P/24P, 173mil

APPLICATION CIRCUIT

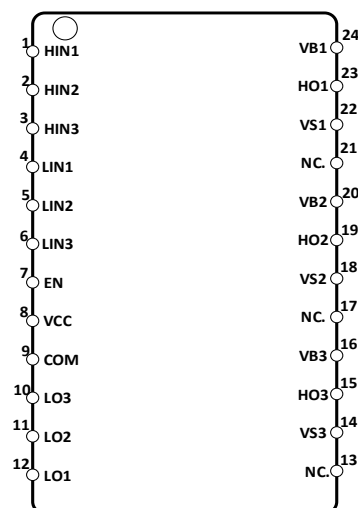


PIN CONFIGURATION

TSSOP20



TSSOP24



PIN DESCRIPTION

Pin Name	Description	Pin No.	
		TSSOP20	TSSOP24
HIN1	Logic input for phase-1 high-side gate driver	1	1
HIN2	Logic input for phase-2 high-side gate driver	2	2
HIN3	Logic input for phase-3 high-side gate driver	3	3
LIN1	Logic input for phase-1 low-side gate driver	4	4
LIN2	Logic input for phase-2 low-side gate driver	5	5
LIN3	Logic input for phase-3 low-side gate driver	6	6
EN	Logic input for standby mode control	-	7
VCC	Logic and low-side gate drivers power supply voltage	7	8
COM	Logic ground and low-side gate drivers ground	8	9
LO3	Phase-3 Low-side gate driver output	9	10
LO2	Phase-2 Low-side gate driver output	10	11
LO1	Phase-1 Low-side gate driver output	11	12
NC.	Not Connected	-	13
VS3	Phase-3 High-side driver floating supply offset voltage	12	14
HO3	Phase-3 High-side driver output	13	15
VB3	Phase-3 High-side driver floating supply	14	16
NC.	Not Connected	-	17
VS2	Phase-2 High-side driver floating supply offset voltage	15	18
HO2	Phase-2 High-side driver output	16	19
VB2	Phase-2 High-side driver floating supply	17	20
NC.	Not Connected	-	21
VS1	Phase-1 High-side driver floating supply offset voltage	18	22
HO1	Phase-1 High-side driver output	19	23
VB1	Phase-1 High-side driver floating supply	20	24

ORDER INFORMATION

Valid Part Number	Package Type	Top Code
PT5618	20 Pins, TSSOP, 173mil	PT5618
PT5618-T1	24 Pins, TSSOP, 173mil	PT5618-T1

FUNCTION DESCRIPTION

LOW SIDE POWER SUPPLY: VCC

VCC is the low side supply and it provides power to both input logic and low side output power stage. The built-in under-voltage lockout circuit enables the device to operate at sufficient power when a typical VCC supply voltage higher than $V_{CCUV+}=8.5V$ is present, shown as FIG1. The IC shuts down all the gate drivers outputs, when the VCC supply voltage is below $V_{CCUV-}=8.0V$, shown as FIG1. This prevents the external power devices against extremely low gate voltage levels during on-state and therefore against excessive power dissipation.

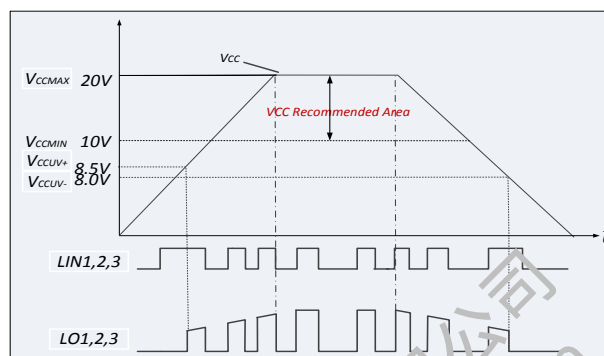


Figure.1: VCC supply UVLO operating area

HIGH SIDE POWER SUPPLY: VBS (VB1-VS1, VB2-VS2, VB3-VS3)

VBS is the high side supply voltage. The totally high side circuitry can float with respect to COM following the external high side power device emitter/source voltage. Due to the internally low power consumption, the whole high side circuitry can be supplied by bootstrap topology connected to VCC, and it can be powered with small bootstrap capacitors.

The device operating area as a function of the supply voltage is given in Figure2.

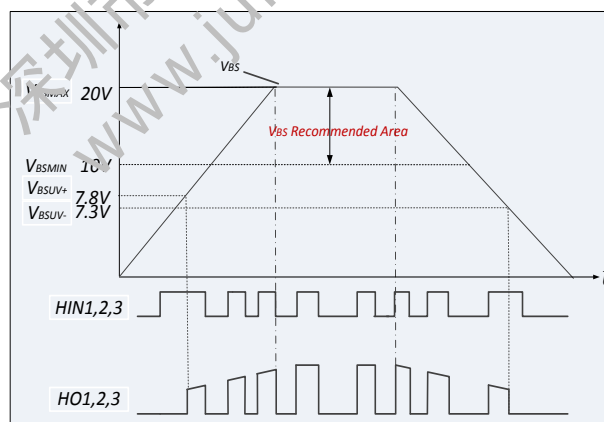


Figure.2: VBS supply UVLO operating area

LOW SIDE AND HIGH CONTROL INPUT LOGIC: HIN&LIN (HIN1, 2, 3/LIN1, 2, 3)

The Schmitt trigger threshold of each input is designed enough low such to guarantee LSTTL and CMOS compatibility down to 3.3 V controller outputs. Input Schmitt trigger and advanced noise filter provide beneficial noise rejection to short input pulses. An internal pull-down resistor of about 100k Ω (positive logic) pre-biases each input during VCC supply start-up state. It is anyway recommended for proper work of the driver not to provide input pulse-width lower than 500ns.

SHOOT-THROUGH PREVENTION

The IC is equipped with shoot-through prevention circuitry (also known as cross conduction prevention circuitry). Figure 3 shows how this prevention circuitry prevents both the high- and low-side switches from conducting at the same time. During the inputs controlling high side driver and low side driver are both “high”, the both driver outputs are pulled down “low” to shutdown two power devices in the same bridge.

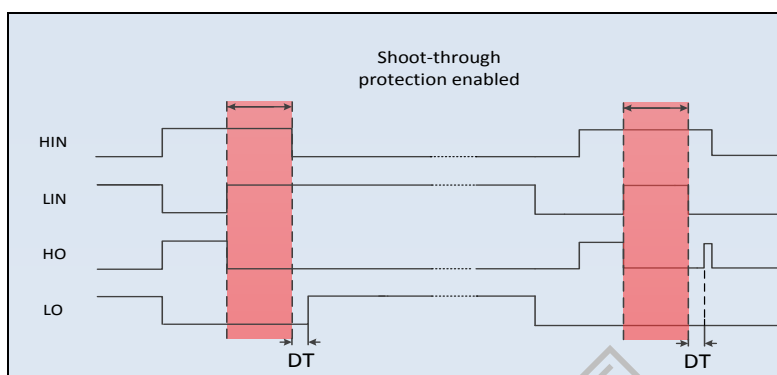


Figure.3: Shoot-through prevention

DEAD TIME

The IC features integrated a fixed dead-time protection circuitry. The dead time feature inserts a time period (a minimum dead time) in which both the high- and low-side power switches are held off; this is done to ensure that the power switch has fully turned off before the second power switch is turned on. This minimum dead time is automatically inserted whenever the external dead time is shorter than DT; external dead times larger than DT are not modified by the gate driver. Figure 4 illustrates the dead time period and the relationship between the output gate signals.

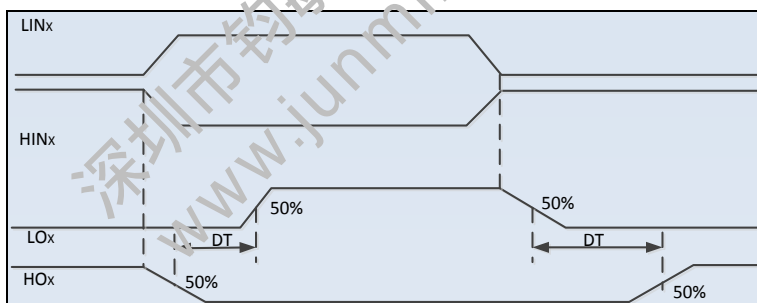


Figure.4: Dead Time

GATE DRIVER (HO1, 2, 3/ LO1, 2, 3)

Low side and high side driver outputs are specifically designed for pulse operation and dedicated to drive the power devices such as IGBT and MOSFET. Low side outputs (i.e. LO1, 2, 3) are state triggered by the respective inputs, while high side outputs (i.e. HO1, 2, 3) are only changed at the edge of the respective inputs. In particular, after releasing from an under voltage condition of the VBS supply, a new turn-on signal (edge) is necessary to activate the respective high side output, while after releasing from a under voltage condition of the VCC supply, the low side outputs can directly switch to the state of their respective inputs and don't suffer from the trouble as high side driver.

STANDBY MODE

This device packed in TSSOP24 provides a featured pin, EN, to enable that it can work into low current dissipation state. EN can be compatible with 5V/3.3V logic level. If EN goes up to “high” level, this device is forced into standby mode, when all gate driver output is locked into “low” level and only 16uA (typ.) is dissipated. If EN goes from “high” level to “low” level, and waits a delay about 3us (typ.), this device can be released from standby mode, and all outputs are enabled. In order to lower the bias current, a 100k Ω , sufficiently large resistor is tied between EN and COM

ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device or make the function abnormal. All the voltage parameters are absolute voltages referenced to IC COM unless otherwise stated in the table.

Parameter	Symbol	Min.	Max.	Units
High-side floating supply voltage	$V_{B1,2,3}$	-0.3	225	V
High-side offset voltage	$V_{S1,2,3}$	$V_{B1,2,3}-25$	$V_{B1,2,3}+0.3$	
High-side gate driver output voltage	$V_{HO1,2,3}$	$V_{S1,2,3}-0.3$	$V_{B1,2,3}+0.3$	
Low-side gate driver output voltage	$V_{LO1,2,3}$	COM-0.3	$V_{CC}+0.3$	
Logic input voltage	$V_{HIN1,2,3}$ $V_{LIN1,2,3}$ EN	-0.3	25	
Low-side supply voltage	V_{CC}	-0.3	25	
Package power dissipation @ $T_A \leq 25^\circ\text{C}$ ¹	P_D	—	TSSOP20:1.2 TSSOP24:1.3	W
Thermal resistance, junction to ambient ¹	R_{thJA}	—	TSSOP20:100 TSSOP24:94	$^\circ\text{C}/\text{W}$
Allowable Offset Voltage Slew Rate	dV/dt	—	50	V/ns
Junction temperature	T_J	-40	+150	$^\circ\text{C}$
Storage temperature	T_S	-40	+150	
Soldering lead temperature (duration 10s)	T_L	—	260	$^\circ\text{C}$

Note 1: P_D and R_{thJA} are only guaranteed by design.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min.	Typ.	Max.	Units
Low-side supply voltage	V_{CC}	10	—	20	V
High-side Floating Supply Offset Voltage ^{2, 3}	$V_{S1,2,3}$	COM-6	—	200	
High-side Floating Supply Voltage	$V_{B1,2,3}$	$V_{S1,2,3}+10$	—	$V_{B1,2,3}+20$	
High-side gate driver output voltage	$V_{HO1,2,3}$	V_S	—	V_B	
Low-side gate driver output voltage	$V_{LO1,2,3}$	COM	—	V_{CC}	
Logic input voltage	$V_{HIN1,2,3}$ $V_{LIN1,2,3}$ EN	0	—	5	
IC operating Junction temperature	T_J	-40	—	+125	$^\circ\text{C}$

Note 2: For $V_{BS}=15\text{V}$, normal Logic operation for V_S of COM-6V to 200V. High-side circuitry will sustain current state if V_S is of COM-6 to COM- V_{BS} . The parameter is only guaranteed by design.

Note 3 IC packed by TSSOP20L is recommended to operate at V_S of -6 to 100V.

STATIC ELECTRICAL CHARACTERISTICS

(V_{CC}-COM)=(V_B-V_S)=15V. Ambient temperature TA=25°C unless otherwise specified. The V_{IN,TH}, V_I, and I_{IN} Parameters are reference to COM and are applicable to all channels. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads. The V_{CCUV} parameters are referenced to COM. The V_{BSUV} parameters are referenced to V_S.

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Low Side Power Supply Characteristics						
Quiescent VCC supply current	I _{QVCC1}	V _{HIN1,2,3} =V _{LIN1,2,3} =0 or 5V, V _{EN} =0	210	330	450	μA
Quiescent VCC supply current in standby mode	I _{QVCC2}	V _{HIN1,2,3} =V _{LIN1,2,3} =0 or 5V, V _{EN} =5	-	16	40	
operating VCC supply current	I _{VCCOP}	f _{LIN1,2,3} =20KHz, f _{HIN1,2,3} =20KHz,	-	1500	-	
VCC supply under-voltage positive going threshold	V _{CCUV+}	-	7.7	8.5	9.5	V
VCC supply under-voltage negative going threshold	V _{CCUV-}	-	7	8.0	9	
VCC supply under-voltage lockout hysteresis	V _{CCHYS}	-	-	0.5	-	
High Side Floating Power Supply Characteristics						
High side VBS supply under-voltage positive going threshold	V _{BSUV+}	-	6.6	7.8	9	V
High side VBS supply under-voltage negative going threshold	V _{BSUV-}	-	6.1	7.3	8.5	
High side VBS supply under-voltage lockout hysteresis	V _{BSUVHYS}	-	-	0.5	-	
High side quiescent VBS supply current	I _{QBS}	V _{BS} =15V	44	63	85	μA
Offset supply leakage current	I _{IK}	V _B =V _S =200V V _{CC} =0V	-	-	10	
Logic Input Section						
Logic"1" Input voltage HIN1,2,3, LIN1,2,3 and EN	V _{IH}	-	2.5	-	-	V
Logic"0" Input voltage HIN1,2,3, LIN1,2,3 and EN	V _{IL}	-	-	-	0.8	
Input positive going threshold	V _{IN,TH+}	-	-	1.9	-	
Input negative going threshold	V _{IN,TH-}	-	-	1.4	-	
Logic "1" Input bias current	I _{IN+}	V _{IN} =5V	-	50	-	μA
Logic "0" Input bias current	I _{IN-}	V _{IN} =0	-	0	-	
Gate Driver Output Section						
High Side Output High Short-Circuit Pulse Current	I _{HO+}	V _{HO} =V _S =0	-	320	-	mA
High Side Output Low Short-Circuit Pulse Current	I _{HO-}	V _{HO} =V _B =15V	-	620	-	
Low Side Output High Short-Circuit Pulse Current	I _{LO+}	V _{LO} =0	-	320	-	
Low Side Output Low Short-Circuit Pulse Current	I _{LO-}	V _{LO} =V _{CC} =15V	-	620	-	
Allowable Negative VS Voltage for HIN1,2,3 Signal Propagation to HO1,2,3	V _{SN}	V _{BS} =15V	-	-8	-	V

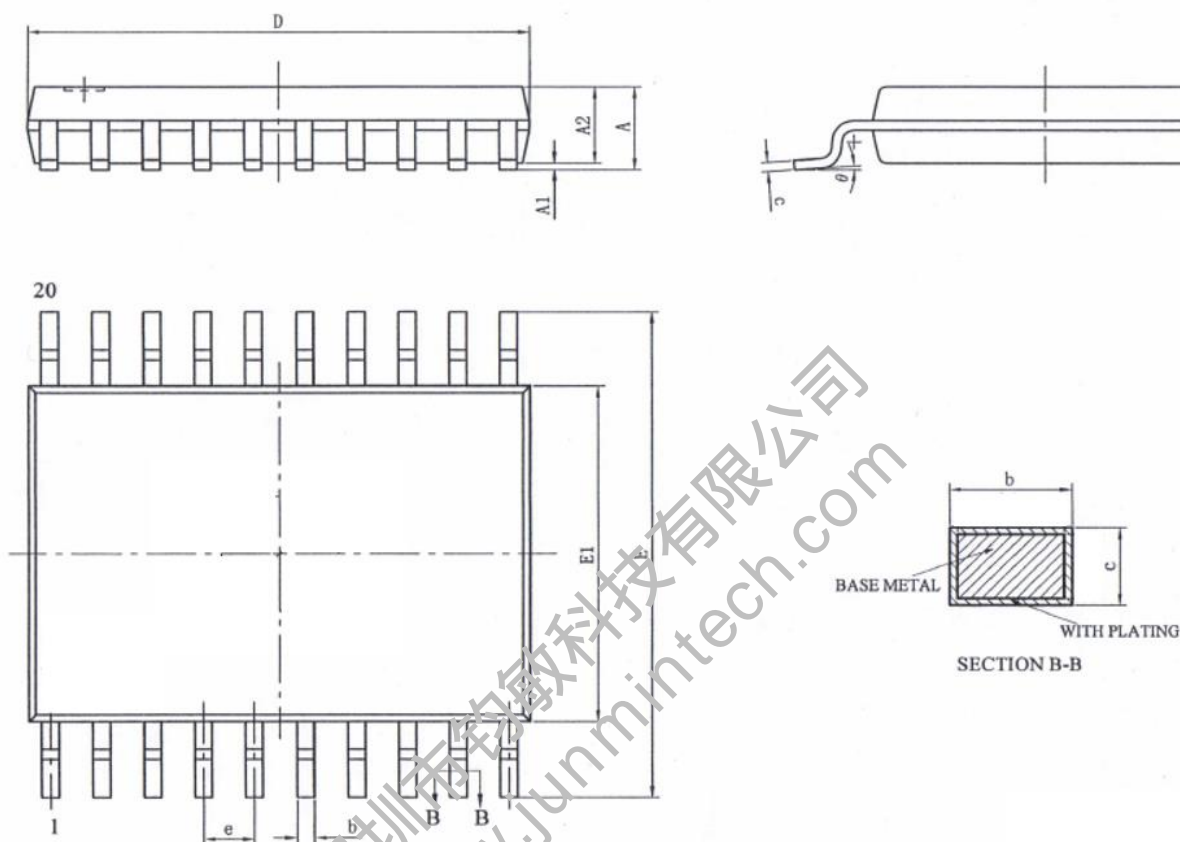
DYNAMIC ELECTRICAL CHARACTERISTICS

(VCC-COM)= (VB-VS) =15V , $V_{S1,2,3}$ =COM, and C_{load} =1nF unless otherwise specified, ambient temperature T_A =25°C.

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Turn-On propagation delay	t_{on}	$V_{HIN1,2,3}$ or $V_{LIN1,2,3}$ =5V, $V_{S1,2,3}$ =0	270	460	650	ns
Turn-Off Propagation delay	t_{off}	$V_{HIN1,2,3}$ or $V_{LIN1,2,3}$ =0, $V_{S1,2,3}$ =0	270	500	650	
Turn-On Rise time	t_r	$V_{HIN1,2,3}$ or $V_{LIN1,2,3}$ =5V, $V_{S1,2,3}$ =0	-	60	-	
Turn-Off Fall time	t_f	$V_{HIN1,2,3}$ or $V_{LIN1,2,3}$ =0, $V_{S1,2,3}$ =0	-	33	-	
Input Filtering Time	$t_{FLT,IN}$	$V_{HIN1,2,3}$ or $V_{LIN1,2,3}$ =0 & 5V	100	300	500	
Dead Time	DT	$V_{HIN1,2,3}$ or $V_{LIN1,2,3}$ =0 & 5V, Without External dead time	400	600	800	
Dead-Time Matching(All Six Channels)	MDT	Without External dead time	-	-	100	
Delay Matching(All Six Channels)	MT	External dead time >1000ns	-	-	100	
Output Pulse-Width Matching	PM	External dead time > 1000ns, $PW_{IN}=10\mu s$, $PM=PW_{OUT}-PW_{IN}$	-	-	100	μs
EN input filter time	$t_{FLT,EN}$	$V_{EN}=0$ & 5V	-	250	-	
EN input "high" to HO/LO turn-off delay time	$t_{off,EN}$	$V_{EN}=5V$	0.5	0.9	-	
EN input "low" to HO/LO turn-on delay time	$t_{on,EN}$	$V_{EN}=0V$	2	3	-	

PACKAGE INFORMATION

20 PINS, TSSOP

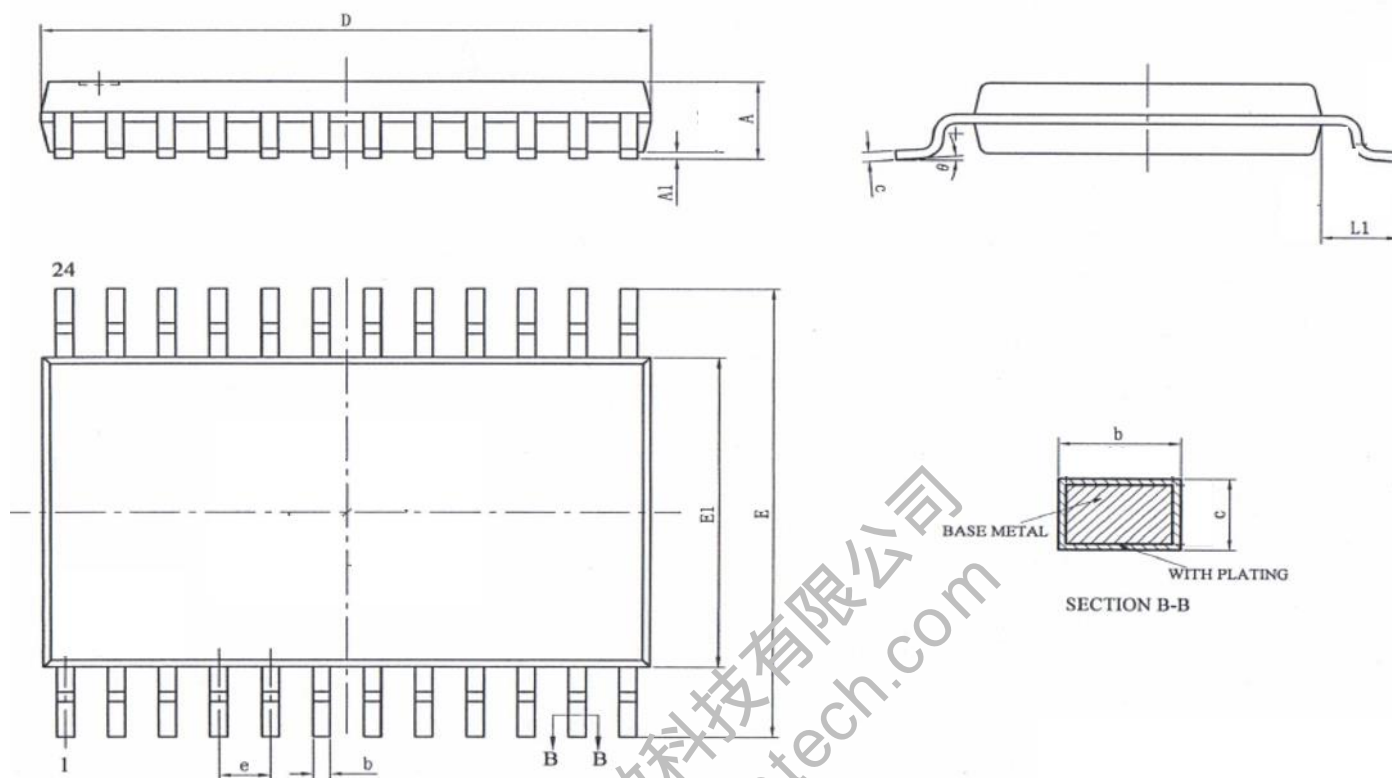


Symbol	Dimensions		
	Min.	Nom.	Max.
A	-	-	1.20
A1	0.05	-	0.15
A2	0.80	1.00	1.05
b	0.19	-	0.30
c	0.09	-	0.20
e	0.65 BSC.		
D	6.40	6.50	6.60
E	6.4 BSC.		
E1	4.30	4.40	4.50
L	0.45	0.60	0.75
L1	1.00 REF		
θ	0°	-	8°

Notes:

1. All dimensions refer to JEDEC MO-153 AC
2. All dimensions are in mm.

24 PINS, TSSOP



Symbol	Dimensions		
	Min.	Nom.	Max.
A	-	-	1.20
A1	0.05	-	0.15
b	0.19	0.20	0.30
c	0.09	-	0.20
e	0.65 BSC.		
D	7.70	7.80	7.90
E	6.20	6.40	6.60
E1	4.30	4.40	4.50
L1	1.00 REF		
θ	0°	-	8°

Notes:

- All dimensions refer to JEDEC MO-153 ADT
- All dimensions are in mm.

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